

MC74VHCT125A

Quad Bus Buffer

with 3-State Control Inputs

The MC74VHCT125A is a high speed CMOS quad bus buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74VHCT125A requires the 3-state control input (\overline{OE}) to be set High to place the output into the high impedance state.

The VHCT inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3 V to 5.0 V, because it has full 5.0 V CMOS level output swings.

The VHCT125A input structures provide protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. The output structures also provide protection when $V_{CC} = 0$ V. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

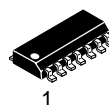
- High Speed: $t_{PD} = 3.8$ ns (Typ) at $V_{CC} = 5.0$ V
- Low Power Dissipation: $I_{CC} = 4.0$ μ A (Max) at $T_A = 25^\circ$ C
- TTL-Compatible Inputs: $V_{IL} = 0.8$ V; $V_{IH} = 2.0$ V
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V Operating Range
- Low Noise: $V_{OLP} = 0.8$ V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:
 - Human Body Model > 2000 V;
 - Machine Model > 200 V
- Chip Complexity: 72 FETs or 18 Equivalent Gates
- Pb-Free Packages are Available*



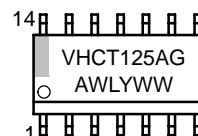
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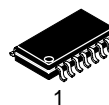
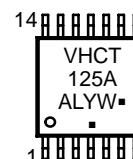
MARKING DIAGRAMS



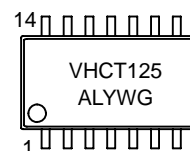
SOIC-14
D SUFFIX
CASE 751A



TSSOP-14
DT SUFFIX
CASE 948G



SOEIAJ-14
M SUFFIX
CASE 965



A	=	Assembly
Location		
L, WL	=	Wafer Lot
Y, YY	=	Year
WW, W	=	Work Week
G or ■	=	Pb-Free Package

(Note: Microdot may be in either location)

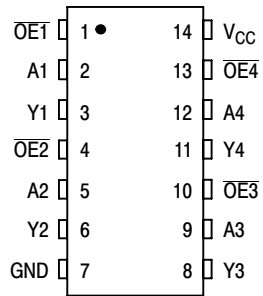
ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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PIN CONNECTION (Top View)

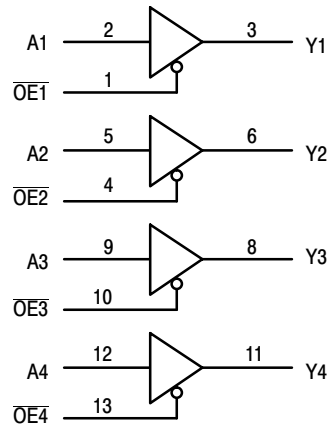


FUNCTION TABLE

VHCT125A		
Inputs		Output
A	OE	Y
H	L	H
L	L	L
X	H	Z

LOGIC DIAGRAM

Active-Low Output Enables



ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHCT125ADR2	SOIC-14	2500 Tape & Reel
MC74VHCT125ADR2G	SOIC-14 (Pb-Free)	2500 Tape & Reel
MC74VHCT125ADTR2	TSSOP-14*	2500 Tape & Reel
MC74VHCT125ADTRG	TSSOP-14*	2500 Tape & Reel
MC74VHCT125AM	SOEIAJ-14	50 Units / Rail
MC74VHCT125AMG	SOEIAJ-14 (Pb-Free)	50 Units / Rail
MC74VHCT125AMEL	SOEIAJ-14	2000 Tape & Reel
MC74VHCT125AMELG	SOEIAJ-14 (Pb-Free)	2000 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*This package is inherently Pb-Free.

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MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V
V _{in}	DC Input Voltage	-0.5 to +7.0	V
V _{out}	DC Output Voltage Output in 3-State High or Low State	-0.5 to +7.0 -0.5 to V _{CC} +0.5	V
I _{IK}	Input Diode Current	-20	mA
I _{OK}	Output Diode Current (V _{OUT} < GND; V _{OUT} > V _{CC})	±20	mA
I _{out}	DC Output Current, per Pin	±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±75	mA
P _D	Power Dissipation in Still Air, SOIC Packages† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature	-65 to +150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating — SOIC Packages: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	4.5	5.5	V
V _{in}	DC Input Voltage	0	5.5	V
V _{out}	DC Output Voltage Output in 3-State High or Low State	0 0	5.5 V _{CC}	V
T _A	Operating Temperature	-55	+125	°C
t _r , t _f	Input Rise and Fall Time V _{CC} = 5.0 V ± 0.5 V	0	20	ns/V

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V _{CC} (V)	T _A = 25°C			T _A ≤ 85°C		T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V _{IH}	Minimum High-Level Input Voltage		3.0	1.2			1.2		1.2		V
			4.5	2.0		2.0		2.0			
			5.5	2.0		2.0		2.0			
V _{IL}	Maximum Low-Level Input Voltage		3.0			0.53		0.53		0.53	V
			4.5			0.8		0.8		0.8	
			5.5			0.8		0.8		0.8	
V _{OH}	Minimum High-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	V _{IN} = V _{IH} or V _{IL} I _{OH} = -50 μA	3.0	2.9	3.0		2.9		2.9		V
			4.5	4.4	4.5		4.4		4.4		
		V _{IN} = V _{IH} or V _{IL} I _{OH} = -4.0 mA I _{OH} = -8.0 mA	3.0	2.58			2.48		2.34		
			4.5	3.94			3.80		3.66		
V _{OL}	Maximum Low-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	V _{IN} = V _{IH} or V _{IL} I _{OL} = 50 μA	3.0		0.0	0.1		0.1		0.1	V
			4.5		0.0	0.1		0.1		0.1	
		V _{IN} = V _{IH} or V _{IL} I _{OL} = 4.0 mA I _{OL} = 8.0 mA	3.0			0.36		0.44		0.52	
			4.5			0.36		0.44		0.52	
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±0.1		μA	
I _{CC}	Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			2.0		20		40	μA
I _{CC(T)}	Quiescent Supply Current	Input: V _{IN} = 3.4 V	5.5			1.35		1.50		1.65	mA
I _{OZ}	Maximum Three-State Leakage Current	V _{IN} = V _{IH} or V _{IL} V _{OUT} = V _{CC} or GND	5.5			±0.25		±2.5		±2.5	μA
I _{OPD}	Output Leakage Current	V _{OUT} = 5.5 V	0.0			0.5		5.0		10	μA

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AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

Symbol	Parameter	Test Conditions	$T_A = 25^\circ\text{C}$			$T_A \leq 85^\circ\text{C}$		$T_A \leq 125^\circ\text{C}$		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_{PLH} , t_{PHL}	Maximum Propagation Delay, A to Y	$V_{CC} = 3.3 \pm 0.3$ V $C_L = 15$ pF $C_L = 50$ pF		5.6 8.1	8.0 11.5	1.0 1.0	9.5 13.0		12.0 16.0	ns
		$V_{CC} = 5.0 \pm 0.5$ V $C_L = 15$ pF $C_L = 50$ pF		3.8 5.3	5.5 7.5	1.0 1.0	6.5 8.5		8.5 10.5	
t_{PZL} , t_{PZH}	Maximum Output Enable Time, OE to Y	$V_{CC} = 3.3 \pm 0.3$ V $C_L = 15$ pF $R_L = 1.0$ k Ω $C_L = 50$ pF		5.4 7.9	8.0 11.5	1.0 1.0	9.5 13.0		11.5 15.0	ns
		$V_{CC} = 5.0 \pm 0.5$ V $C_L = 15$ pF $R_L = 1.0$ k Ω $C_L = 50$ pF		3.6 5.1	5.1 7.1	1.0 1.0	6.0 8.0		7.5 9.5	
t_{PLZ} , t_{PHZ}	Maximum Output Disable Time, $\overline{\text{OE}}$ to Y	$V_{CC} = 3.3 \pm 0.3$ V $C_L = 50$ pF $R_L = 1.0$ k Ω		9.5	13.2	1.0	15.0		18.0	ns
		$V_{CC} = 5.0 \pm 0.5$ V $C_L = 50$ pF $R_L = 1.0$ k Ω		6.1	8.8	1.0	10.0		12.0	
t_{OSLH} , t_{OSHL}	Output-to-Output Skew	$V_{CC} = 3.3 \pm 0.3$ V $C_L = 50$ pF (Note 1)			1.5		1.5		2.0	ns
		$V_{CC} = 5.0 \pm 0.5$ V $C_L = 50$ pF (Note 1)			1.0		1.0		1.5	
C_{in}	Maximum Input Capacitance			4	10		10		10	pF
C_{out}	Maximum Three-State Output Capacitance (Output in High Impedance State)			6						pF

C_{PD}	Power Dissipation Capacitance (Note 2)	Typical @ 25°C , $V_{CC} = 5.0\text{V}$				pF
		14				

- Parameter guaranteed by design. $t_{OSLH} = |t_{PLHm} - t_{PLHn}|$, $t_{OSHL} = |t_{PHLm} - t_{PHLn}|$.
- C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \cdot V_{CC} \cdot f_{in} + I_{CC}/4$ (per buffer). C_{PD} is used to determine the no-load dynamic power consumption; $P_D = C_{PD} \cdot V_{CC}^2 \cdot f_{in} + I_{CC} \cdot V_{CC}$.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 5.0$ V)

Symbol	Characteristic	$T_A = 25^\circ\text{C}$		Unit
		Typ	Max	
V_{OLP}	Quiet Output Maximum Dynamic V_{OL}	0.3	0.8	V
V_{OLV}	Quiet Output Minimum Dynamic V_{OL}	-0.3	-0.8	V
V_{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V_{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

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SWITCHING WAVEFORMS

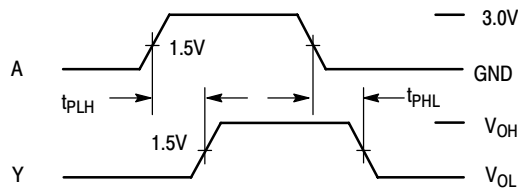


Figure 1.

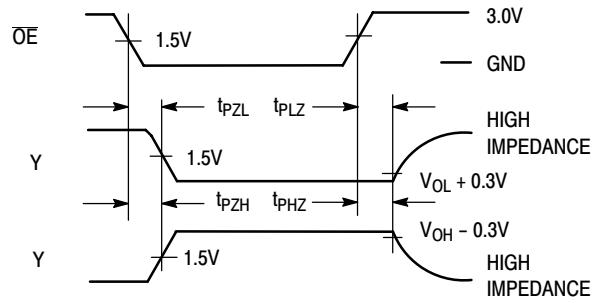
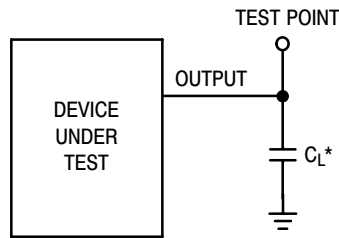
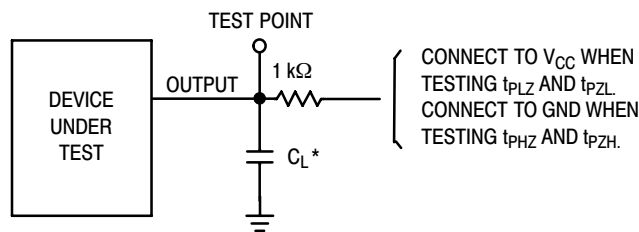


Figure 2.



*Includes all probe and jig capacitance

Figure 3. Test Circuit



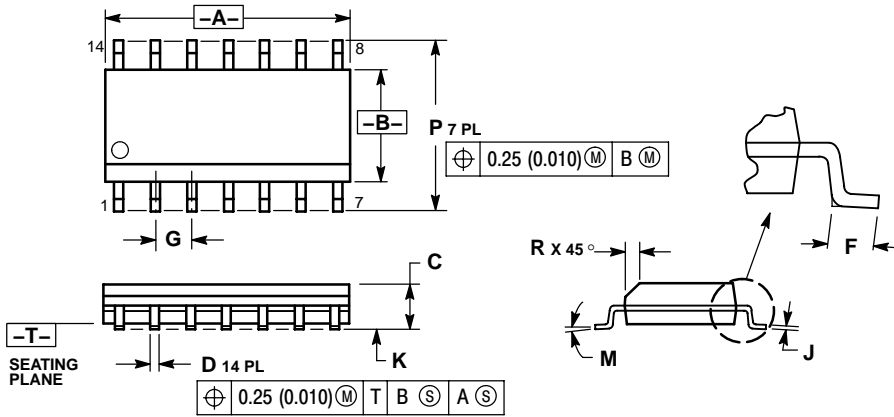
*Includes all probe and jig capacitance

Figure 4. Test Circuit

MC74VHCT125A

PACKAGE DIMENSIONS

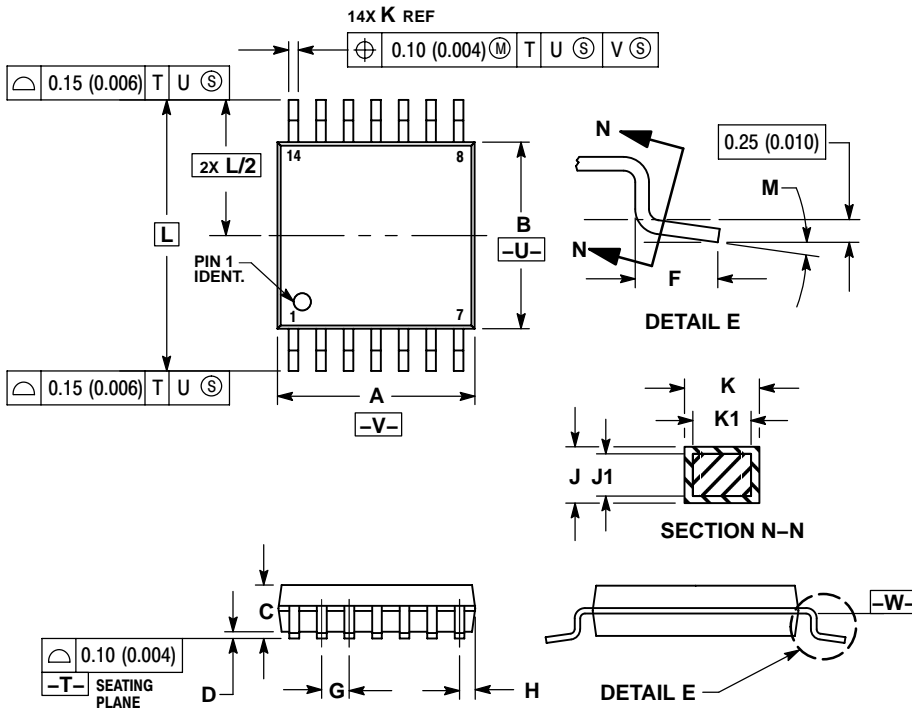
SOIC-14
D SUFFIX
CASE 751A-03
ISSUE G



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

TSSOP-14
DT SUFFIX
CASE 948G-01
ISSUE A



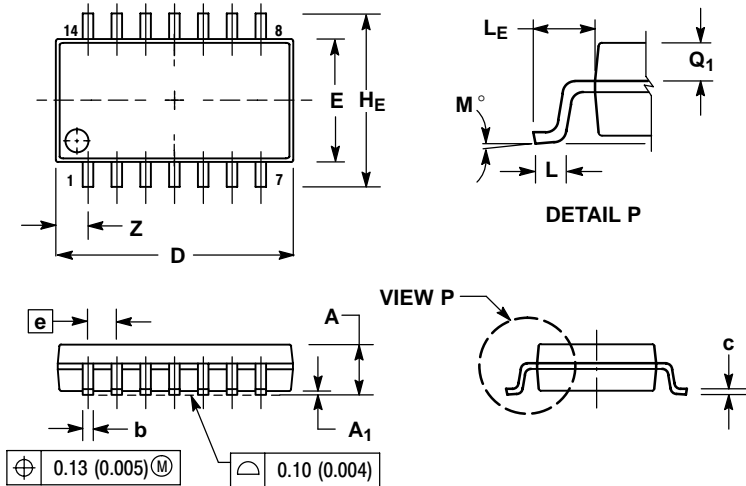
- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

MC74VHCT125A

PACKAGE DIMENSIONS

SOEIAJ-14
M SUFFIX
CASE 965-01
ISSUE A



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.10	0.20	0.004	0.008
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H _E	7.40	8.20	0.291	0.323
0.50	0.50	0.85	0.020	0.033
L _E	1.10	1.50	0.043	0.059
M	0°	10°	0°	10°
Q ₁	0.70	0.90	0.028	0.035
Z	---	1.42	---	0.056

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